



SI7495DP-T1-E3 Information



For Reference Only

Part Number SI7495DP-T1-E3 **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 12V 13A PPAK SO-8

Package PowerPAK? SO-8

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SI7495DP-T1-E3 Specifications

| Manufacturer Part NumberSI7495DP-T1-E3ManufacturerVishay SiliconixCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackagePowerPAK? SO-8SeriesTrenchFET?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)12VCurrent - Continuous Drain (Id) @ 25°C13A (Ta)Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id900mV @ 1mAGate Charge (Qg) (Max) @ Vgs140nC @ 5VInput Capacitance (Ciss) (Max) @ Vds±8VYgs (Max)±8VFET Feature-Power Dissipation (Max)1.8W (Ta)Rds On (Max) @ Id, Vgs6.5 mOhm @ 21A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8Peckage / CasePowerPAK? SO-8 | | |
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| Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package PowerPAK? SO-8 Series TrenchFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 12V Current - Continuous Drain (Id) @ 25°C 13A (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 140nC @ 5V Input Capacitance (Ciss) (Max) @ Vds ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case | Manufacturer Part Number | SI7495DP-T1-E3 |
| Package PowerPAK? SO-8 Series TrenchFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 12V Current - Continuous Drain (Id) @ 25°C 13A (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 900mV @ ImA Gate Charge (Qg) (Max) @ Vgs 140nC @ 5V Input Capacitance (Ciss) (Max) @ Vds ±8V FET Feature - Power Dissipation (Max) 1.8W (Ta) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 21A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8 | Manufacturer | Vishay Siliconix |
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| SeriesTrenchFET?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)12VCurrent - Continuous Drain (Id) @ 25°C13A (Ta)Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id900mV @ 1mAGate Charge (Qg) (Max) @ Vgs140nC @ 5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±8VFET Feature-Power Dissipation (Max)1.8W (Ta)Rds On (Max) @ Id, Vgs6.5 mOhm @ 21A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8 | | Transistors - FETs, MOSFETs - Single |
| FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 12V Current - Continuous Drain (Id) @ 25°C 13A (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 900mV @ 1mA Gate Charge (Qg) (Max) @ Vgs 140nC @ 5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 1.8W (Ta) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 21A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case | Package | PowerPAK? SO-8 |
| Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 13A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package PowerPAK? SO-8 PowerPAK? SO-8 Package / Case MAX (Ta) MOSFET (Metal Oxide) 12V MOSFET (Metal Oxide) 12V MOSFET (Metal Oxide) 12V 12V 12V 12V 12V 13A (Ta) 1.8V (4.5V 900mV @ 1mA 1.8V (© 5V 1.8V (Ta) 6.5 mOhm @ 21A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Surface Mount Supplier Device Package PowerPAK? SO-8 | Series | TrenchFET? |
| Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 13A (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 900mV @ 1mA Gate Charge (Qg) (Max) @ Vgs 140nC @ 5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case | FET Type | P-Channel |
| Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 900mV @ 1mA Gate Charge (Qg) (Max) @ Vgs 140nC @ 5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±8V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 21A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case | Technology | MOSFET (Metal Oxide) |
| Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package PowerPAK? SO-8 Package / Case 1.8V, 4.5V 900mV @ 1mA 140nC @ 5V | Drain to Source Voltage (Vdss) | 12V |
| Vgs(th) (Max) @ Id 900mV @ 1mA Gate Charge (Qg) (Max) @ Vgs 140nC @ 5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 1.8W (Ta) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 21A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8 | Current - Continuous Drain (Id) @ 25°C | 13A (Ta) |
| Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds | Drive Voltage (Max Rds On, Min Rds On) | 1.8V, 4.5V |
| Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) EET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case PowerPAK? SO-8 | Vgs(th) (Max) @ Id | 900mV @ 1mA |
| Vgs (Max)±8VFET Feature-Power Dissipation (Max)1.8W (Ta)Rds On (Max) @ Id, Vgs6.5 mOhm @ 21A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8 | Gate Charge (Qg) (Max) @ Vgs | 140nC @ 5V |
| FET Feature - Power Dissipation (Max) 1.8W (Ta) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 21A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8 | Input Capacitance (Ciss) (Max) @ Vds | - |
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| Rds On (Max) @ Id, Vgs6.5 mOhm @ 21A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePowerPAK? SO-8Package / CasePowerPAK? SO-8 | FET Feature | - |
| Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8 | Power Dissipation (Max) | 1.8W (Ta) |
| Mounting Type Surface Mount Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8 | Rds On (Max) @ Id, Vgs | 6.5 mOhm @ 21A, 4.5V |
| Supplier Device Package PowerPAK? SO-8 Package / Case PowerPAK? SO-8 | Operating Temperature | -55°C ~ 150°C (TJ) |
| Package / Case PowerPAK? SO-8 | Mounting Type | Surface Mount |
| | Supplier Device Package | PowerPAK? SO-8 |
| Report errors? | Package / Case | PowerPAK? SO-8 |
| | | Report errors? |

SI7495DP-T1-E3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SI7495DP-T1-E3 Payment Methods



















SI7495DP-T1-E3 Shipping Methods













If you have any question about SI7495DP-T1-E3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com